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Markus Pessa received the Ph.D. degree from the University of Turku, Turku, Finland, in 1972.

He is the Founder and Director of the Optoelectronics Research Centre (ORC), Tampere University of Technology, Tampere, Finland, the largest organization of optoelectronics and ultra-fast optics in Finland, where he is also a Professor of semiconductor technology. He has played a seminal role in establishing laser fabrication industry in Finland. He has authored **400 journal articles** on optoelectronics, semiconductor physics, electron spectroscopy, and surface science.

Dr. Pessa was elected a Foreign Associate of the United States National Academy of Engineering (NAE) in 2006, as the first Finnish citizen. He is a Knight, First Class, of the Order of the White Rose of Finland, awarded by the President of the Republic of Finland, 1996, and was designated Professor of the Year (Finland) by the Trade Union of University Professors, 1998. He is a Member of the Editorial Boards of *New Journal of Physics* (London) and *IEE Optics Proceedings* (London). He is also a Member of the Board of Directors of the Kista Photonics Research Center (Royal Institute of Technology, Sweden) and the Finnish Cultural Institute in Tokyo (Japan), and is a Fellow of the Institute of Physics (London).

Total no. of Citation (without self-citation): >2000

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